

Title (en)

Method for producing a gallium phosphide epitaxial wafer.

Title (de)

Verfahren zur Herstellung eines epitaktischen Wafers.

Title (fr)

Méthode de fabrication d'une plaquette epitaxiée.

Publication

EP 0654832 A1 19950524 (EN)

Application

EP 94307788 A 19941024

Priority

JP 29165693 A 19931122

Abstract (en)

A method for producing a GaP epitaxial wafer used for fabrication of light emitting diodes having higher brightness than light emitting diodes fabricated from a GaP epitaxial wafer produced by a conventional method. The method comprises the steps of: preparing a GaP layered substrate (15) with one or more GaP layers on a GaP single crystal substrate (10) in the first series of liquid phase epitaxial growth; obtaining a layered GaP substrate (15a) by eliminating surface irregularities of said GaP layered substrate (15) by mechano-chemical polishing to make the surface to be planar; and then forming a GaP light emitting layer composite (19) on said layered GaP substrate (15a) in the second series of liquid phase epitaxial growth. <IMAGE> <IMAGE>

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IPC 8 full level

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CPC (source: EP US)

H01L 33/0062 (2013.01 - EP US); **H01L 33/30** (2013.01 - EP US)

Citation (search report)

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DE FR GB

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